BC817-40W

45 V, 0.5 A, General Purpose NPN Transistor

ON Semiconductor's BC817–40W is a General Purpose NPN Transistor that is housed in the SC–70/SOT–323 package.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This Device is Pb–Free, Halogen Free/BFR Free and is RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

| Rating | Symbol | Value | Unit |
|--------------------------------|------------------|-------|------|
| Collector – Emitter Voltage | V _{CEO} | 45 | V |
| Collector – Base Voltage | V _{CBO} | 50 | V |
| Emitter – Base Voltage | V _{EBO} | 5.0 | V |
| Collector Current – Continuous | Ic | 500 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------------------------|-------------|------|
| Total Device Dissipation (Note 1) | P _D | 460 | mW |
| Thermal Resistance, Junction-to-Ambient (Note 1) | $R_{\theta JA}$ | 272 | °C/W |
| Junction and Storage Temperature Range | T _J , T _{stg} | -55 to +150 | °C |

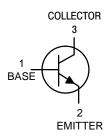
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 Board, 1 oz. Cu, 100 mm²



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SC-70 CASE 419 STYLE 3

MARKING DIAGRAM



CE = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION[†]

| Device | Package | Shipping |
|-----------------|--------------------|-----------------------|
| BC817-40WT1G | SC-70 (Pb-Free) | 3000 / Tape & Reel |
| NSVBC817-40WT1G | SC-70 (Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

BC817-40W

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit | |
|--|----------------------|-----------|--------|------------|----------|--|
| OFF CHARACTERISTICS | | | | | | |
| Collector – Emitter Breakdown Voltage (I _C = 10 mA) | V _{(VR)CEO} | 45 | _ | _ | V | |
| Collector – Emitter Breakdown Voltage (V _{EB} = 0 V, I _C = 10 μA) | V _{(VR)CES} | 50 | _ | - | V | |
| Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$) | V _{(VR)EBO} | 5.0 | _ | - | V | |
| Collector Cutoff Current $(V_{CB} = 20 \text{ V})$ $(V_{CB} = 20 \text{ V}, T_A = 150^{\circ}\text{C})$ | I _{CBO} | | _ _ | 100 5.0 | nA μA | |
| ON CHARACTERISTICS | | | | | | |
| DC Current Gain (Note 2) $(I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V})$ $(I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V})$ | h _{FE} | 250 40 | | 600 - | - | |
| Collector – Emitter Saturation Voltage (Note 2) $(I_C = 500 \text{ mA}, I_B = 50 \text{ mA})$ | V _{CE(sat)} | - | _ | 0.7 | V | |
| Base – Emitter On Voltage (Note 2) ($I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$) | V _{BE(on)} | - | _ | 1.2 | V | |
| SMALL-SIGNAL CHARACTERISTICS | | | | | | |
| Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz) | f _T | 100 | _ | - | MHz | |
| Output Capacitance $(V_{CB} = 10 \text{ V}, f = 1.0 \text{ MHz})$ | C _{obo} | - | 10 | - | pF | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Condition: Pulse Width = 300 μ sec, Duty Cycle \leq 2%

BC817-40W

TYPICAL CHARACTERISTICS

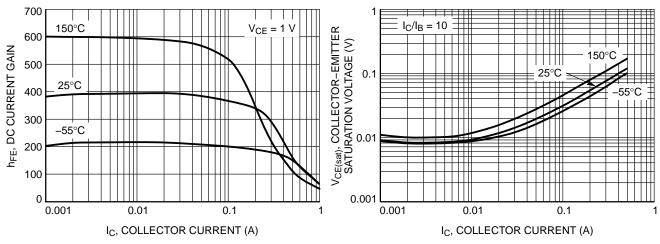


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

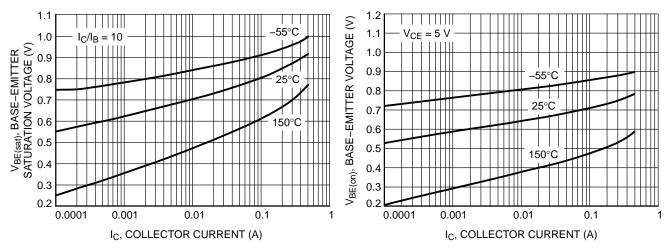


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Voltage vs. Collector Current

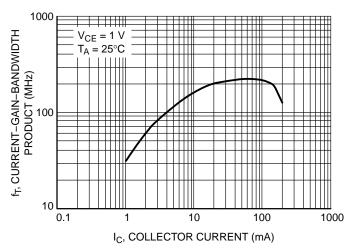
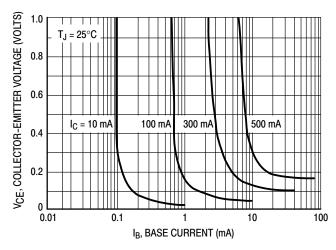


Figure 5. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS



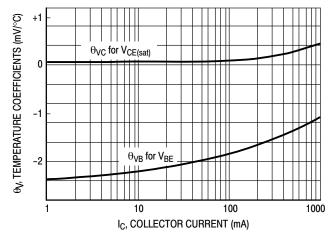


Figure 6. Saturation Region

Figure 7. Temperature Coefficients

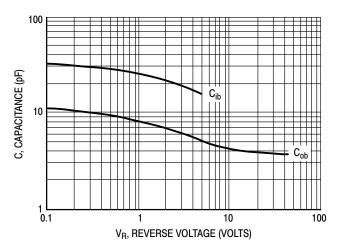


Figure 8. Capacitances

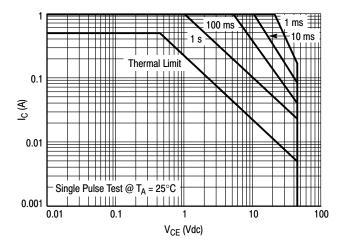


Figure 9. Safe Operating Area





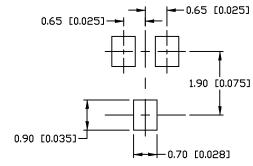
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DATE 07 OCT 2021

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

| | MILLIMETERS | | | | INCHES | | |
|-------------------|----------------------|----------------------------------|----------------------|-------------------------|-------------------------------------|-----------------|--|
| DIM | MIN. | N□M. | MAX. | MIN. | N□M. | MAX. | |
| Α | 0.80 | 0.90 | 1.00 | 0.032 | 0.035 | 0.040 | |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 | |
| A2 | | 0.70 REF | | | 0.028 BSC | | |
| b | 0.30 | 0.35 | 0.40 | 0.012 | 0.014 | 0.016 | |
| С | 0.10 | 0.18 | 0.25 | 0.004 | 0.007 | 0.010 | |
| D | 1.80 | 2.10 | 2.20 | 0.071 | 0.083 | 0.087 | |
| E | 1.15 | 1.24 | 1.35 | 0.045 | 0.049 | 0.053 | |
| e | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 | |
| e1 | 0.65 BSC | | | | 0.026 BS | C | |
| L | 0.20 | 0.38 | 0.56 | 0.008 | 0.015 | 0.022 | |
| HE | 2.00 | 2.10 | 2.40 | 0.079 | 0.083 | 0.095 | |
| E e e1 L | 1.15 1.20 0.20 | 1.24 1.30 0.65 BS0 0.38 | 1.35 1.40 0.56 | 0.045 0.047 0.008 | 0.049 0.051 0.026 BS 0.015 | 0.0 0.0 C | |



For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

TOP VIEW SIDE VIEW END VIEW

GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| STYLE 1: CANCELLED | STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE | STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE | |
|-----------------------|---|---|--|--|----------------|
| STYLE 6: | STYLE 7: | STYLE 8: | STYLE 9: | STYLE 10: | STYLE 11: |
| PIN 1. EMITTER | PIN 1. BASE | PIN 1. GATE | PIN 1. ANODE | PIN 1. CATHODE | PIN 1. CATHODE |
| 2. BASE | 2. EMITTER | 2. SOURCE | 2. CATHODE | 2. ANODE | 2. CATHODE |
| 3. COLLECTOR | 3. COLLECTOR | 3. DRAIN | 3. CATHODE-ANODE | 3. ANODE-CATHODE | 3. CATHODE |

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| DESCRIPTION: | SC-70 (SOT-323) | | PAGE 1 OF 1 | |

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